



SEP8506-002

SEP Series GaAs Infrared Emitting Diode, Side-emitting Plastic Package

Features

- Side-emitting plastic package
- 50 ° (nominal) beam angle
- 935 nm wavelength
- Mechanically and spectrally matched to SDP8406 phototransistor, SDP8106 photodarlington and SDP8000/8600 series Schmitt trigger

Description

The SEP8506 is a gallium arsenide infrared emitting diode molded in a side-emitting red plastic package. The chip is positioned to emit radiation through a plastic lens from the side of the package.

Representative photograph, actual product appearance may vary.

Due to regional agency approval requirements, some products may not be available in your area.

Please contact your regional Honeywell office regarding your product of choice.

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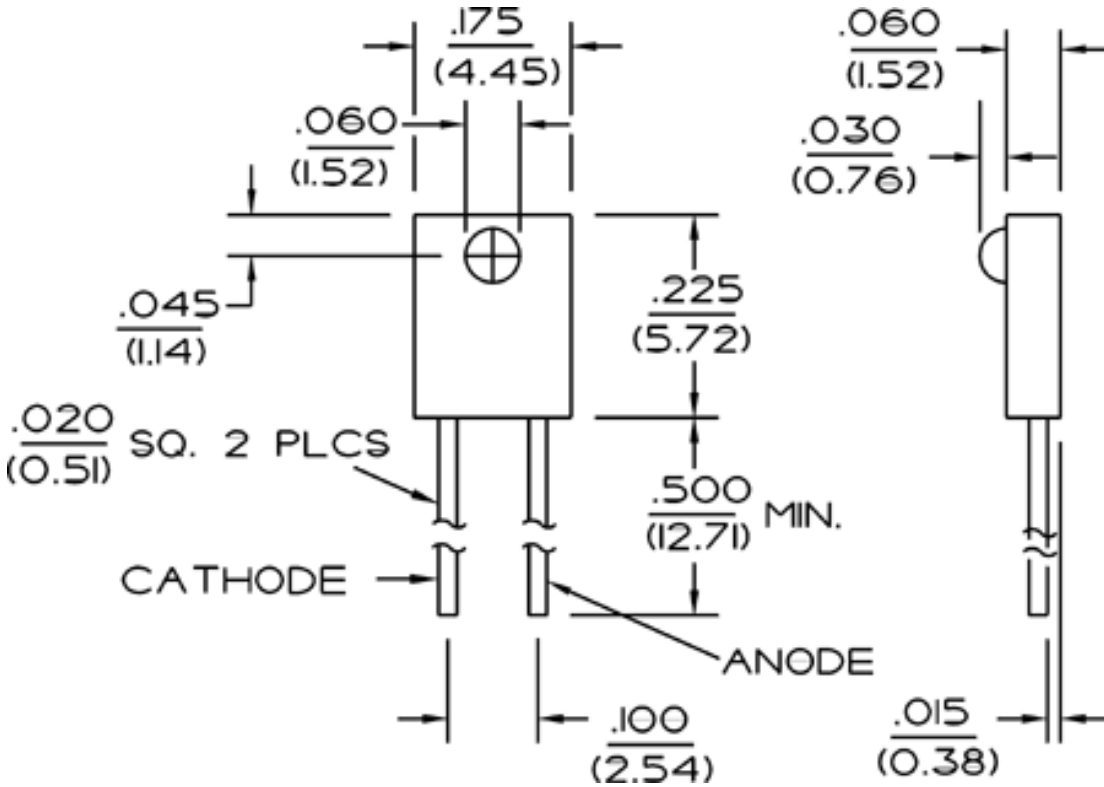
Product Specifications	
Product Type	IR Component
Power Output	0.33 - 0.52 mW/cm ²
Beam Angle (Degree)	50
Package Style	Side-Emitting
Package Components	Plastic
Forward Current	20 mA
Continuous Forward Current	50 mA
Forward Voltage	1.5 V
Reverse Breakdown Voltage	3 V
Output Wavelength	935 nm
Spectral Bandwidth	50 nm
Spectral Shift With Temperature	0.3 nm/°C
Rise and Fall Time	0.7 μs
Power Dissipation	100 mW
Operating Temperature Range	-40 °C to 85 °C [-40 °F to 185 °F]

Availability	Global
Product Name	Infrared Emitting Diode

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